

## Silicon Epitaxial Planar Transistor

## M8550

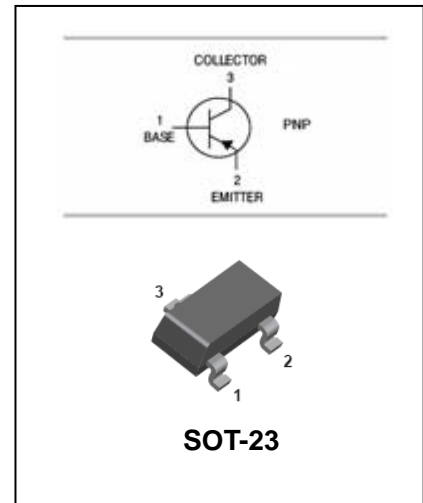
### FEATURES

- High Collector Current.( $I_C = -800$  mA).
- Complementary To M8050.
- Excellent  $H_{FE}$  Linearity.



### APPLICATIONS

- High Collector Current.



### ORDERING INFORMATION

Type No.	Marking	Package Code
M8550	Y21	SOT-23

### MAXIMUM RATING @ $T_a = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current -Continuous	-800	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

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**M8550**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-35V, I_E=0$		-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-20V, I_B=0$		-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-1V, I_C=-5mA$	45		
		$V_{CE}=-1V, I_C=-100mA$	85	300	
		$V_{CE}=-1V, I_C=-800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$		-1.2	V
Transition frequency	$f_T$	$V_{CE}=-6V, I_C=-20mA$ $f=30MHz$	150		MHz

**CLASSIFICATION OF  $h_{FE(1)}$**

Rank	L	H
Range	85-200	200-300

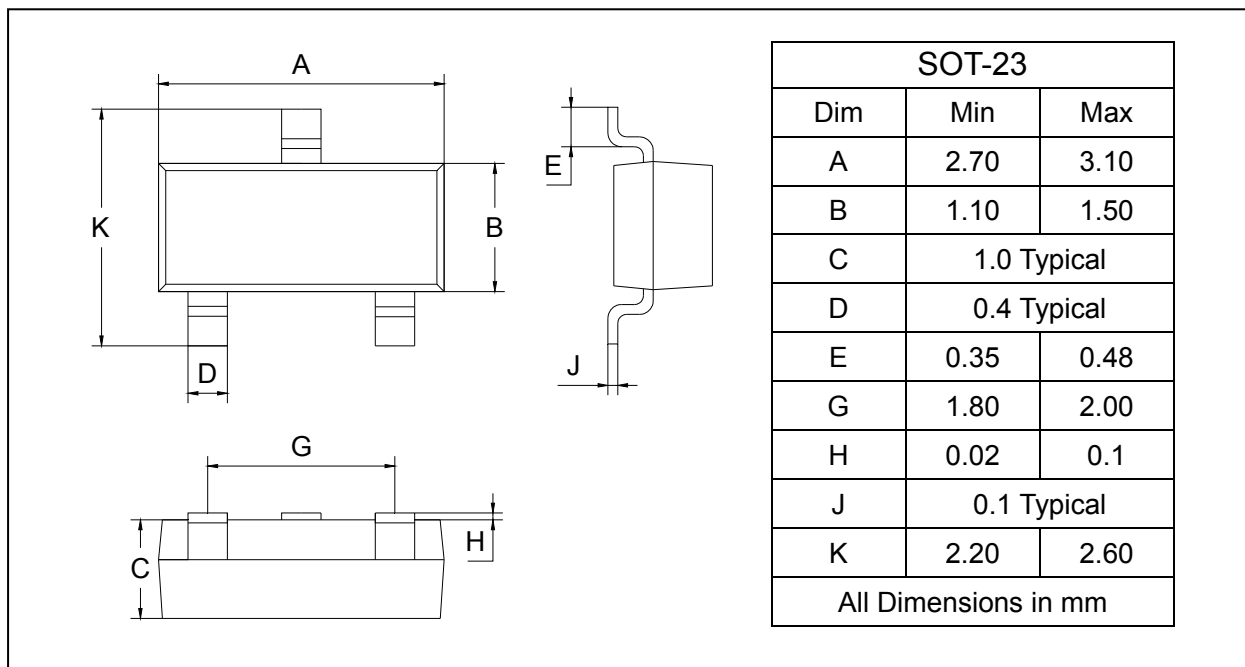
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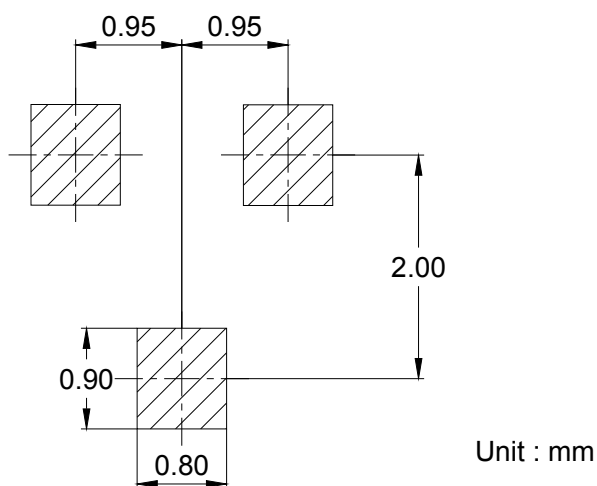
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
M8550	SOT-23	3000/Tape&Reel